

ESD Protection diode

RSB6.8S

●Application

Noise suppression on signal line

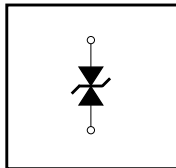
●Features

- 1) Small surface mounting type. (EMD2)
- 2) High reliability.

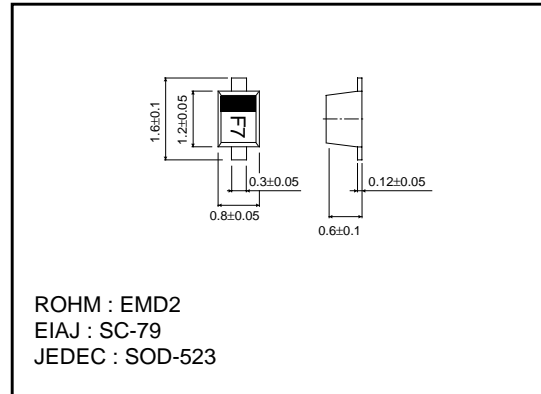
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak pulse power (tp=10×1000μs)	Ppk	10	W
Power dissipation	P	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C
Operation temperature	Topr	-55~+150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Zener voltage	Vz	5.780	—	7.820	V	Iz=1mA
Reverse current	Ir	—	—	0.5	μA	VR=3.5V
Junction capacitance	Ct	—	30	—	pF	VR=0V, F=1MHz

*Zener voltage (Vz) shall be measured at 40ms after loading current.

Diodes

●Others

Item	IEC-61000-4-2
Equipment composition	Charge discharge capacitance : 150pF Discharge resistance : 330Ω
Criterion	Repeat by 10 times No erroneous operation Contact : ±8kV In air : ±15kV

●Electrical characteristic curves (Ta=25°C)

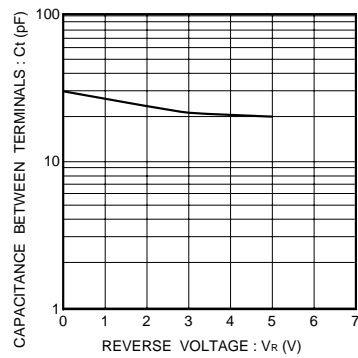


Fig.1 Capacitance between terminals characteristics

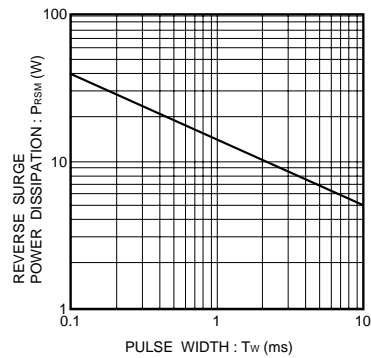


Fig.2 Surge power dissipation